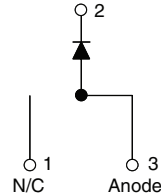


## HEXFRED®

### Ultrafast Soft Recovery Diode, 4 A


**D-PAK**

**FEATURES**

- Ultrafast recovery time
- Ultrasoft recovery
- Very low  $I_{RRM}$
- Very low  $Q_{rr}$
- Guaranteed avalanche
- Specified at operating temperature
- Lead (Pb)-free
- Designed and qualified for Q101 level


**RoHS\***  
 COMPLIANT

**BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

**DESCRIPTION/APPLICATIONS**

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

**PRODUCT SUMMARY**

$V_R$	600 V
$V_F$ at 4 A at 25 °C	1.8 V
$I_{F(AV)}$	4 A
$t_{rr}$ (typical)	17 ns
$T_J$ (maximum)	150 °C

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	$V_{RRM}$		600	V
Maximum continuous forward current	$I_{F(AV)}$	$T_C = 100\text{ °C}$	4	A
Single pulse forward current	$I_{FSM}$		25	
Repetitive peak forward current	$I_{FRM}$	$T_C = 116\text{ °C}$	16	
Maximum power dissipation	$P_D$	$T_C = 100\text{ °C}$	10	W
Operating junction and storage temperatures	$T_J, T_{Stg}$		- 55 to 150	°C

**ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$  unless otherwise specified)**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_R$	$I_R = 100\ \mu\text{A}$	600	-	-	V
Forward voltage See fig. 1	$V_F$	$I_F = 4\text{ A}$	-	1.5	1.8	
		$I_F = 8\text{ A}$	-	1.8	2.2	
Maximum reverse leakage current	$I_R$	$V_R = V_R$ rated	-	0.17	3.0	$\mu\text{A}$
		$T_J = 125\text{ °C}, V_R = 0.8 \times V_R$ rated	-	44	300	
Junction capacitance	$C_T$	$V_R = 200\text{ V}$	-	4	8	pF
Series inductance	$L_S$	Measured lead to lead 5 mm from package body	-	8.0	-	nH

\* Pb containing terminations are not RoHS compliant, exemptions may apply

DYNAMIC RECOVERY CHARACTERISTICS ( $T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	$t_{rr}$	$I_F = 1.0\text{ A}$ , $di_F/dt = 200\text{ A}/\mu\text{A}$ , $V_R = 30\text{ V}$	-	17	-	ns
		$T_J = 25\text{ }^\circ\text{C}$	-	28	42	
		$T_J = 125\text{ }^\circ\text{C}$	-	38	57	
Peak recovery current	$I_{RRM}$	$T_J = 25\text{ }^\circ\text{C}$	-	2.9	5.2	A
		$T_J = 125\text{ }^\circ\text{C}$	-	3.7	6.7	
Reverse recovery charge	$Q_{rr}$	$T_J = 25\text{ }^\circ\text{C}$	-	40	60	nC
		$T_J = 125\text{ }^\circ\text{C}$	-	70	105	
Rate of fall of recovery current	$di_{(rec)M}/dt$	$T_J = 25\text{ }^\circ\text{C}$	-	280	-	A/ $\mu\text{s}$
		$T_J = 125\text{ }^\circ\text{C}$	-	235	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		- 55	-	150	$^\circ\text{C}$
Soldering temperature	$T_S$	10 s	-	-	240	$^\circ\text{C}/\text{W}$
Thermal resistance, junction to case	$R_{thJC}$		-	-	5.0	
Thermal resistance, junction to ambient	$R_{thJA}$	Typical socket mount	-	-	80	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D-PAK	HFA04SD60S			

## HEXFRED® Ultrafast Soft Recovery Diode, 4 A

Vishay High Power Products

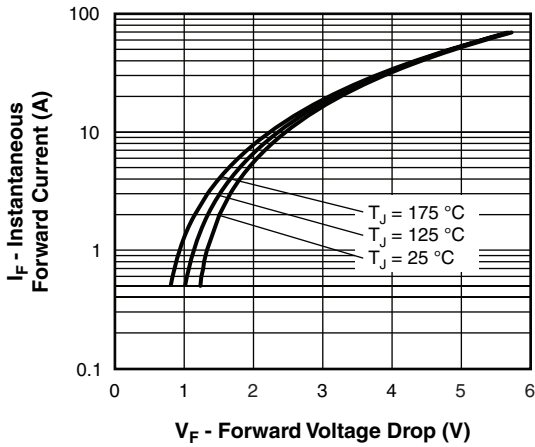


Fig. 1 - Typical Forward Voltage Drop Characteristics

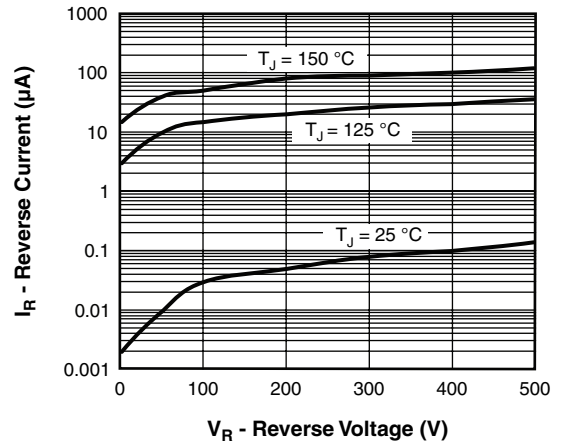


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

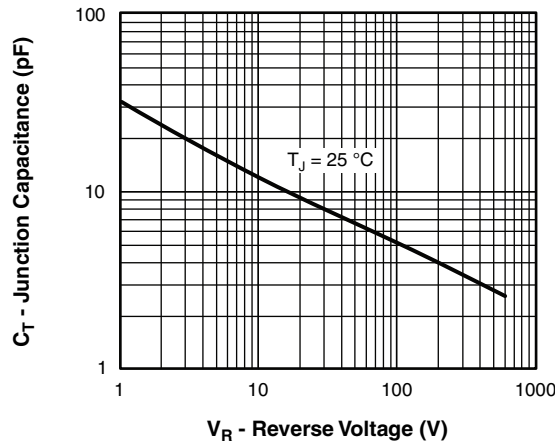


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

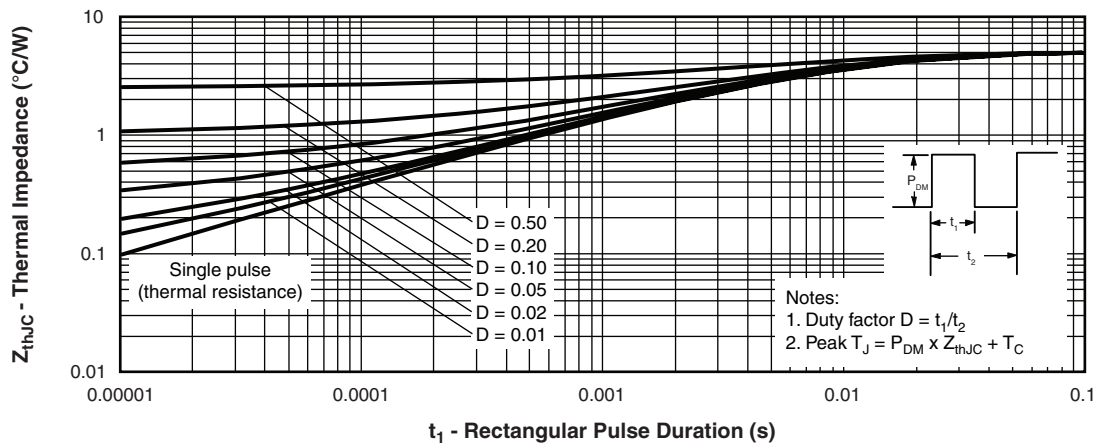


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

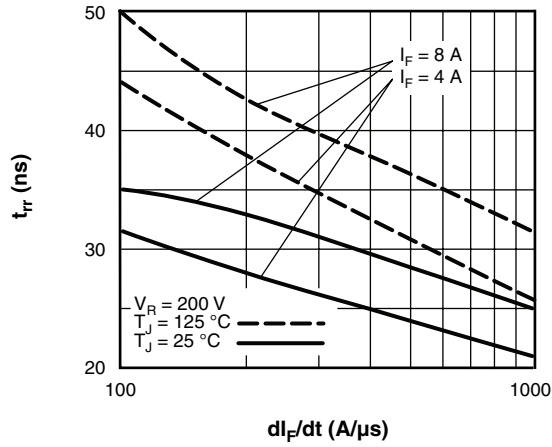


Fig. 5 - Typical Reverse Recovery Time vs.  $dI_F/dt$

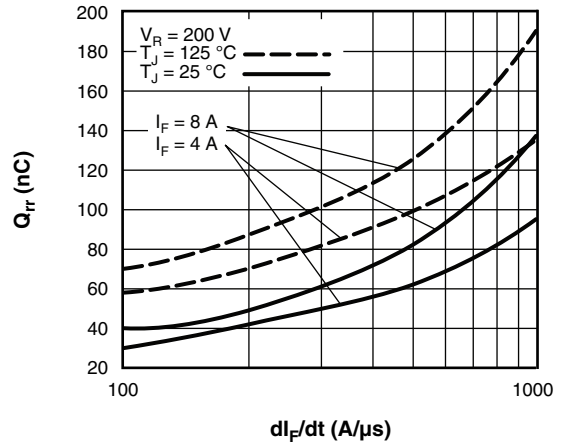


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$

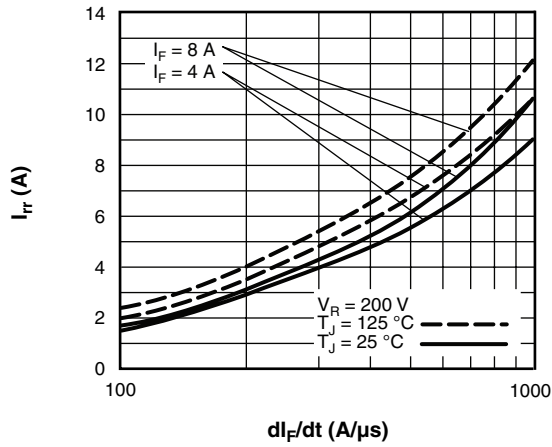


Fig. 6 - Typical Recovery Current vs.  $dI_F/dt$

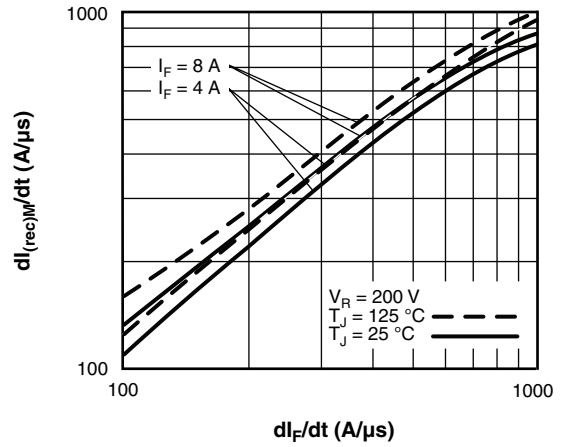


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$

**HEXFRED®**  
 Ultrafast Soft Recovery Diode, 4 A

Vishay High Power Products

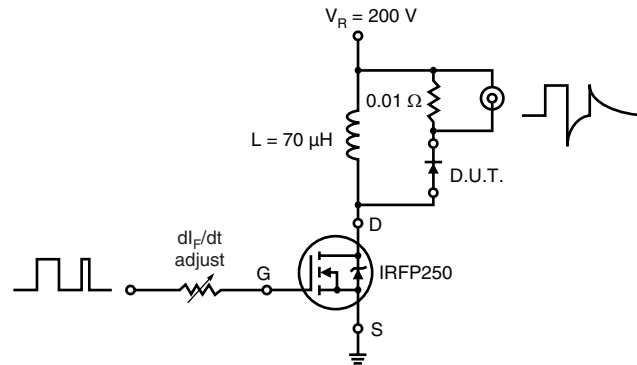
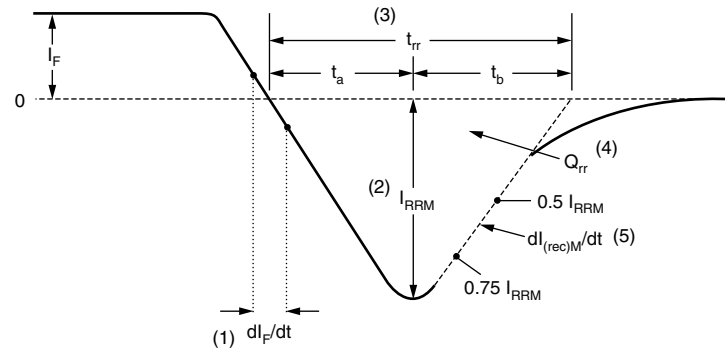


Fig. 9 - Reverse Recovery Parameter Test Circuit


 (1)  $di_f/dt$  - rate of change of current through zero crossing

 (2)  $I_{RRM}$  - peak reverse recovery current

 (3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.

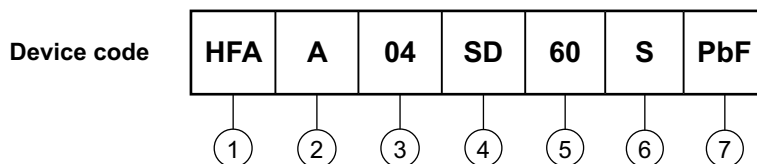
 (4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$ 

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

 (5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

## ORDERING INFORMATION TABLE



- |   |                                |
|---|--------------------------------|
| 1 | - HEXFRED® family              |
| 2 | - Electron irradiated          |
| 3 | - Current rating (04 = 4 A)    |
| 4 | - D-PAK                        |
| 5 | - Voltage rating (60 = 600 V)  |
| 6 | - Suffix                       |
| 7 | - • None = Standard production |
- S = D<sup>2</sup>PAK/D-PAK  
 TR = Tape and reel  
 TRL = Tape and reel left  
 TRR = Tape and reel right
- PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95016">http://www.vishay.com/doc?95016</a>
Part marking information	<a href="http://www.vishay.com/doc?95059">http://www.vishay.com/doc?95059</a>
Packaging information	<a href="http://www.vishay.com/doc?95033">http://www.vishay.com/doc?95033</a>



## Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.